LMC6492 Dual/LMC6494 Quad CMOS Rail-to-Rail Input and Output Operational Amplifier

Check for Samples: LMC6492, LMC6494

FEATURES

(Typical Unless Otherwise Noted)

- **Rail-to-Rail Input Common-Mode Voltage Range, Ensured Over Temperature**
- **Rail-to-Rail Output Swing within 20 mV of Supply Rail, 100 kΩ Load**
- **Operates from 5V to 15V Supply**
- **Excellent CMRR and PSRR 82 dB**
- **Ultra Low Input Current 150 fA**
- **High Voltage Gain (R_L = 100 kΩ) 120 dB**
- **Low Supply Current (@ V_S = 5V) 500 µA/Amplifier**
- **Low Offset Voltage Drift 1.0 µV/°C**

APPLICATIONS

- **Automotive Transducer Amplifier**
- **Pressure Sensor**
- **Oxygen Sensor**
- **Temperature Sensor**
- **Speed Sensor**

DESCRIPTION

The LMC6492/LMC6494 amplifiers were specifically developed for single supply applications that operate from −40°C to +125°C. This feature is well-suited for automotive systems because of the wide temperature range. A unique design topology enables the LMC6492/LMC6494 common-mode voltage range to accommodate input signals beyond the rails. This eliminates non-linear output errors due to input signals exceeding a traditionally limited common-mode voltage range. The LMC6492/LMC6494 signal range has a high CMRR of 82 dB for excellent accuracy in non-inverting circuit configurations.

The LMC6492/LMC6494 rail-to-rail input is complemented by rail-to-rail output swing. This assures maximum dynamic signal range which is particularly important in 5V systems.

Ultra-low input current of 150 fA and 120 dB open loop gain provide high accuracy and direct interfacing with high impedance sources.

Connection Diagram

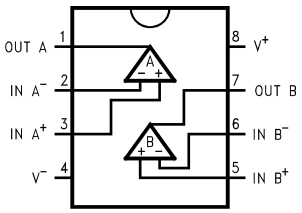


Figure 1. 8-Pin PDIP/SOIC - Top View

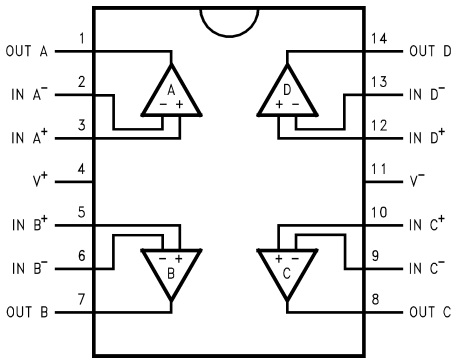


Figure 2. 14-Pin PDIP/SOIC - Top View

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Absolute Maximum Ratings(1)(2)

ESD Tolerance(3)	2000V
Differential Input Voltage	±Supply Voltage
Voltage at Input/Output Pin	(V^+) + 0.3V, (V^-) − 0.3V
Supply Voltage $(V^+ - V^-)$	16V
Current at Input Pin	±5 mA
Current at Output Pin(4)	±30 mA
Current at Power Supply Pin	40 mA
Lead Temp. (Soldering, 10 sec.)	260°C
Storage Temperature Range	−65°C to +150°C
Junction Temperature(5)	150°C

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured. For ensured specifications and the test conditions, see the Electrical Characteristics.
(2) If Military/Aerospace specified devices are required, please contact the TI Sales Office/ Distributors for availability and specifications.
(3) Human body model, 1.5 kΩ in series with 100 pF.
(4) Applies to both single-supply and split-supply operation. Continuous short operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature at 150°C. Output currents in excess of ±30 mA over long term may adversely affect reliability.
(5) The maximum power dissipation is a function of $T_{J(max)}$, θ_{JA} and T_A. The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(max)} - T_A)/\theta_{JA}$. All numbers apply for packages soldered directly into a PC board.

Operating Conditions(1)

Supply Voltage		$2.5V \le V^+ \le 15.5V$
Junction Temperature Range	LMC6492AE, LMC6492BE	$-40°C \le T_J \le +125°C$
	LMC6494AE, LMC6494BE	$-40°C \le T_J \le +125°C$
Thermal Resistance (θ_{JA})	P Package, 8-Pin PDIP	108°C/W
	D Package, 8-Pin SOIC	171°C/W
	P Package, 14-Pin PDIP	78°C/W
	D Package, 14-Pin SOIC	118°C/W

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured. For ensured specifications and the test conditions, see the Electrical Characteristics.

DC Electrical Characteristics

Unless otherwise specified, all limits specified for T_J = 25°C, V^+ = 5V, V^- = 0V, $V_{CM} = V_O = V^+/2$ and R_L > 1 MΩ. **Boldface** limits apply at the temperature extremes

Symbol	Parameter	Conditions	Typ(1)	LMC6492AE LMC6494AE Limit(2)	LMC6492BE LMC6494BE Limit(2)	Units
V_{OS}	Input Offset Voltage		0.11	3.0 **3.8**	6.0 **6.8**	mV max
TCV_{OS}	Input Offset Voltage Average Drift		1.0			µV/°C
I_B	Input Bias Current	See(3)	0.15	**200**	**200**	pA max
I_{OS}	Input Offset Current	See(3)	0.075	**100**	**100**	pA max
R_{IN}	Input Resistance		>10			Tera Ω

(1) Typical Values represent the most likely parametric norm.
(2) All limits are specified by testing or statistical analysis.
(3) Specified limits are dictated by tester limits and not device performance. Actual performance is reflected in the typical value.

DC Electrical Characteristics (continued)

Unless otherwise specified, all limits specified for T_J = 25°C, V^+ = 5V, V^- = 0V, $V_{CM} = V_O = V^+/2$ and R_L > 1 MΩ. **Boldface** limits apply at the temperature extremes

Symbol	Parameter	Conditions		Typ[1]	LMC6492AE LMC6494AE Limit[2]	LMC6492BE LMC6494BE Limit[2]	Units
C_{IN}	Common-Mode Input Capacitance			3			pF
CMRR	Common-Mode Rejection Ratio	0V ≤ V_{CM} ≤ 15V V^+ = 15V		82	65 **60**	63 **58**	dB min
		0V ≤ V_{CM} ≤ 5V		82	65 **60**	63 **58**	
+PSRR	Positive Power Supply Rejection Ratio	5V ≤ V^+ ≤ 15V, V_O = 2.5V		82	65 **60**	63 **58**	dB min
−PSRR	Negative Power Supply Rejection Ratio	0V ≤ V^- ≤ −10V, V_O = 2.5V		82	65 **60**	63 **58**	dB min
V_{CM}	Input Common-Mode Voltage Range	V^+ = 5V and 15V For CMRR ≥ 50 dB		V^- −0.3	−0.25 **0**	−0.25 **0**	V max
				V^+ + 0.3	V^+ + 0.25 **V^+**	V^+ + 0.25 **V^+**	V min
A_V	Large Signal Voltage Gain	R_L = 2 kΩ:[4]	Sourcing	300			V/mV
			Sinking	40			min
V_O	Output Swing	V^+ = 5V R_L = 2 kΩ to $V^+/2$		4.9	4.8 **4.7**	4.8 **4.7**	V min
				0.1	0.18 **0.24**	0.18 **0.24**	V max
		V^+ = 5V R_L = 600Ω to $V^+/2$		4.7	4.5 **4.24**	4.5 **4.24**	V min
				0.3	0.5 **0.65**	0.5 **0.65**	V max
		V^+ = 15V R_L = 2 kΩ to $V^+/2$		14.7	14.4 **14.0**	14.4 **14.0**	V min
				0.16	0.35 **0.5**	0.35 **0.5**	V max
		V^+ = 15V R_L = 600Ω to $V^+/2$		14.1	13.4 **13.0**	13.4 **13.0**	V min
				0.5	1.0 **1.5**	1.0 **1.5**	V max
I_{SC}	Output Short Circuit Current V^+ = 5V	Sourcing, V_O = 0V		25	16 **10**	16 **10**	mA min
		Sinking, V_O = 5V		22	11 **8**	11 **8**	
I_{SC}	Output Short Circuit Current V^+ = 15V	Sourcing, V_O = 0V		30	28 **20**	28 **20**	
		Sinking, V_O = 5V[5]		30	30 **22**	30 **22**	

(4) V^+ = 15V, V_{CM} = 7.5V and R_L connected to 7.5V. For Sourcing tests, 7.5V ≤ V_O ≤ 11.5V. For Sinking tests, 3.5V ≤ V_O ≤ 7.5V.
(5) Do not short circuit output to V^+, when V^+ is greater than 13V or reliability will be adversely affected.

DC Electrical Characteristics (continued)

Unless otherwise specified, all limits specified for T_J = 25°C, V^+ = 5V, V^- = 0V, $V_{CM} = V_O = V^+/2$ and R_L > 1 MΩ. **Boldface** limits apply at the temperature extremes

Symbol	Parameter	Conditions	Typ (1)	LMC6492AE LMC6494AE Limit (2)	LMC6492BE LMC6494BE Limit (2)	Units
I_S	Supply Current	LMC6492	1.0	1.75	1.75	mA
		V^+ = +5V, $V_O = V^+/2$		**2.1**	**2.1**	max
		LMC6492	1.3	1.95	1.95	mA
		V^+ = +15V, $V_O = V^+/2$		**2.3**	**2.3**	max
		LMC6494	2.0	3.5	3.5	mA
		V^+ = +5V, $V_O = V^+/2$		**4.2**	**4.2**	max
		LMC6494	2.6	3.9	3.9	mA
		V^+ = +15V, $V_O = V^+/2$		**4.6**	**4.6**	max

AC Electrical Characteristics

Unless otherwise specified, all limits specified for T_J = 25°C, V^+ = 5V, V^- = 0V, $V_{CM} = V_O = V^+/2$ and R_L > 1 MΩ. **Boldface** limits apply at the temperature extremes

Symbol	Parameter	Conditions	Typ (1)	LMC6492AE LMC6494AE Limit (2)	LMC6492BE LMC6494BE Limit (2)	Units
SR	Slew Rate	See (3)	1.3	0.7	0.7	Vμs min
				0.5	**0.5**	
GBW	Gain-Bandwidth Product	V^+ = 15V	1.5			MHz
φ_m	Phase Margin		50			Deg
G_m	Gain Margin		15			dB
	Amp-to-Amp Isolation	See (4)	150			dB
e_n	Input-Referred Voltage Noise	F = 1 kHz V_{CM} = 1V	37			nV/√HZ
i_n	Input-Referred Current Noise	F = 1 kHz	0.06			pA/√HZ
T.H.D.	Total Harmonic Distortion	F = 1 kHz, A_V = −2 R_L = 10 kΩ, V_O = −4.1 V_{PP}	0.01			%
		F = 10 kHz, A_V = −2 R_L = 10 kΩ, V_O = 8.5 V_{PP} V^+ = 10V	0.01			

(1) Typical Values represent the most likely parametric norm.
(2) All limits are specified by testing or statistical analysis.
(3) V^+ = 15V. Connected as voltage follower with 10V step input. Number specified is the slower of the positive and negative slew rates.
(4) Input referred, V^+ = 15V and R_L = 100 kΩ connected to 7.5V. Each amp excited in turn with 1 kHz to produce V_O = 12 V_{PP}.

Typical Performance Characteristics

V_S = +15V, Single Supply, T_A = 25°C unless otherwise specified

Supply Current vs Supply Voltage

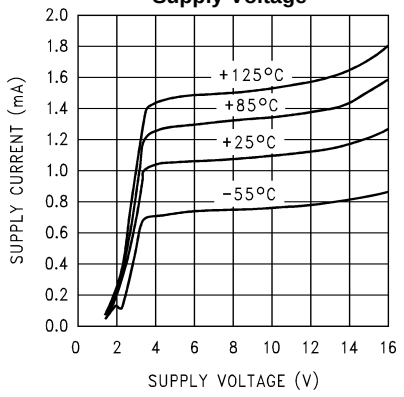


Figure 3.

Input Current vs Temperature

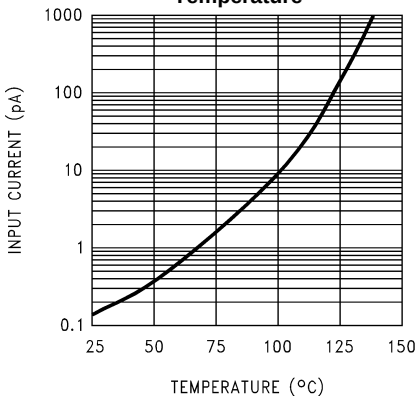


Figure 4.

Sourcing Current vs Output Voltage

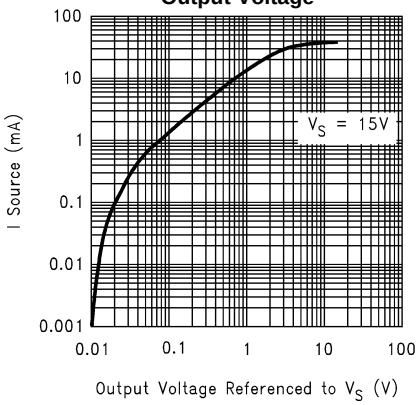


Figure 5.

Sourcing Current vs Output Voltage

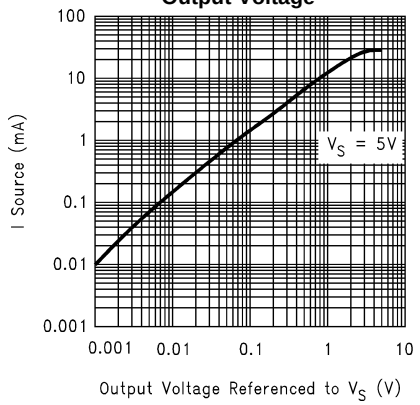


Figure 6.

Sourcing Current vs Output Voltage

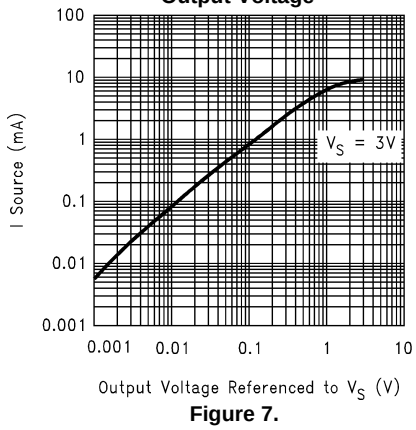


Figure 7.

Sinking Current vs Output Voltage

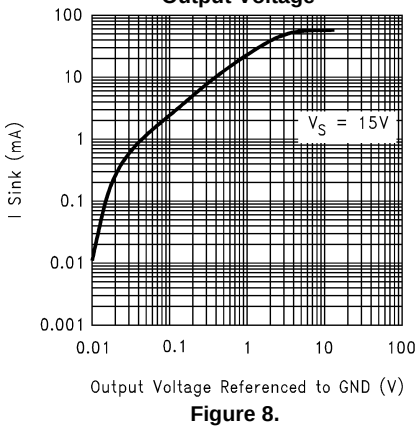


Figure 8.

Typical Performance Characteristics (continued)

V_S = +15V, Single Supply, T_A = 25°C unless otherwise specified

Sinking Current vs Output Voltage

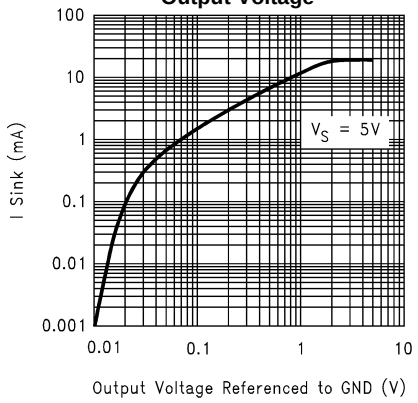


Figure 9.

Sinking Current vs Output Voltage

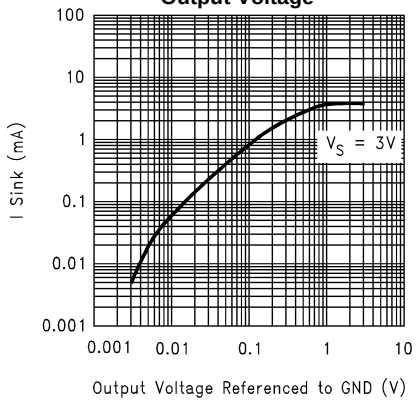


Figure 10.

Output Voltage Swing vs Supply Voltage

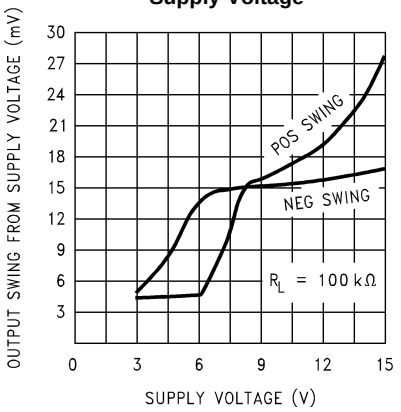


Figure 11.

Input Voltage Noise vs Frequency

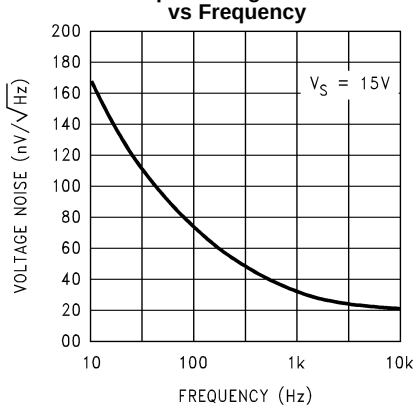


Figure 12.

Input Voltage Noise vs Input Voltage

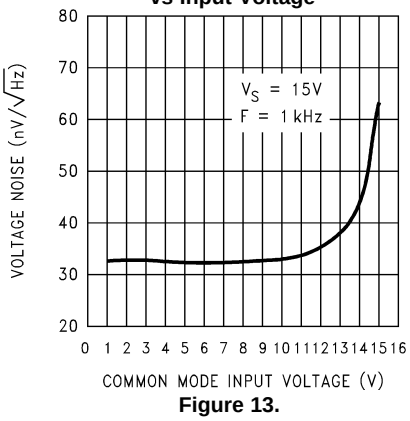


Figure 13.

Input Voltage Noise vs Input Voltage

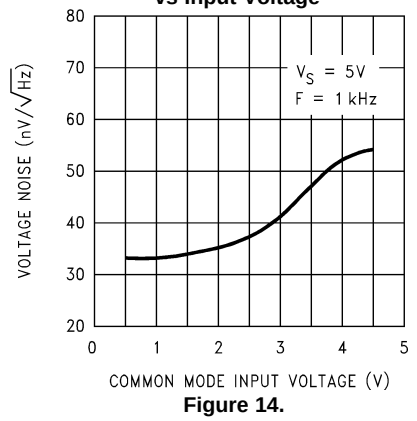


Figure 14.

Typical Performance Characteristics (continued)

V_S = +15V, Single Supply, T_A = 25°C unless otherwise specified

Input Voltage Noise vs Input Voltage

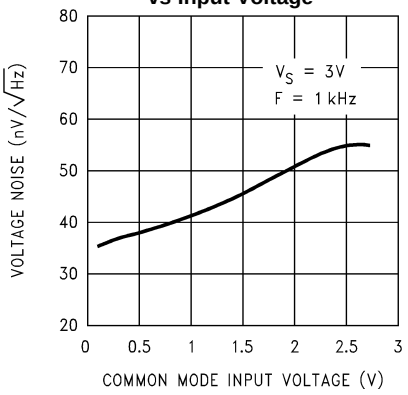


Figure 15.

Crosstalk Rejection vs Frequency

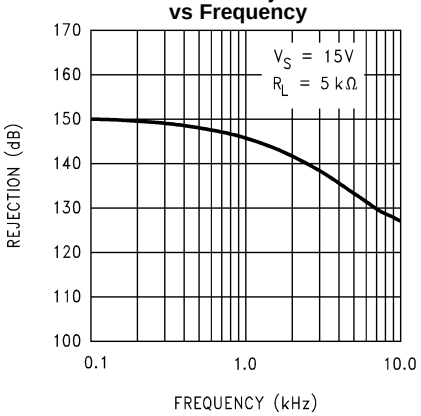


Figure 16.

Crosstalk Rejection vs Frequency

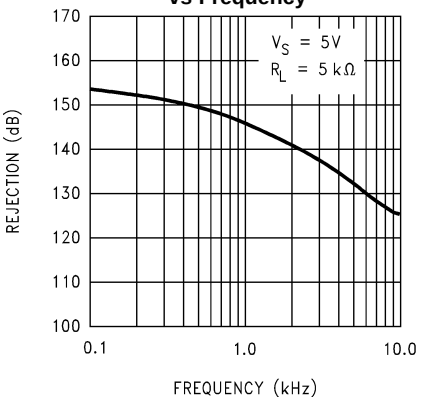


Figure 17.

Positive PSRR vs Frequency

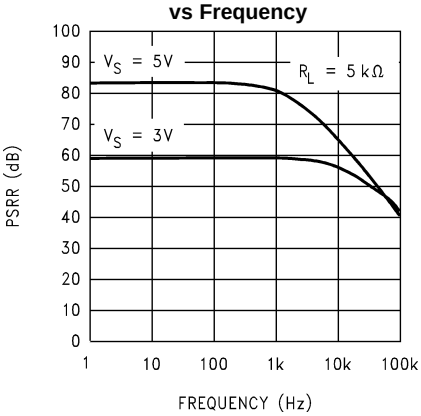


Figure 18.

Negative PSRR vs Frequency

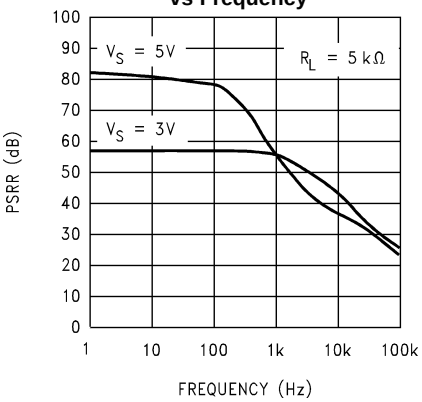


Figure 19.

CMRR vs Frequency

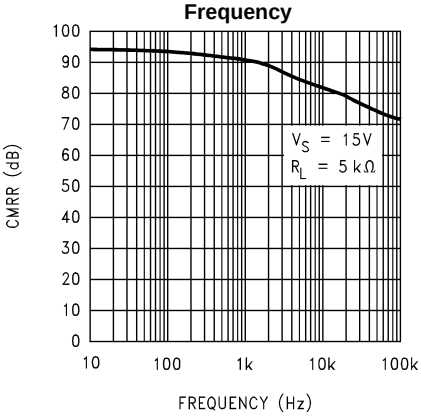


Figure 20.

Typical Performance Characteristics (continued)

V_S = +15V, Single Supply, T_A = 25°C unless otherwise specified

CMRR vs Input Voltage

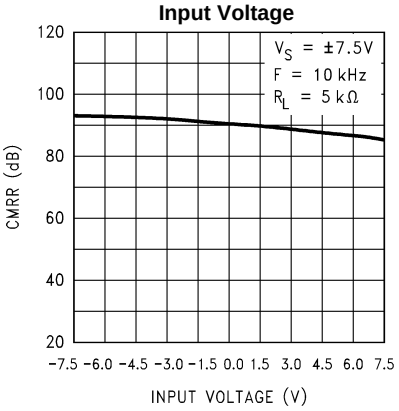


Figure 21.

CMRR vs Input Voltage

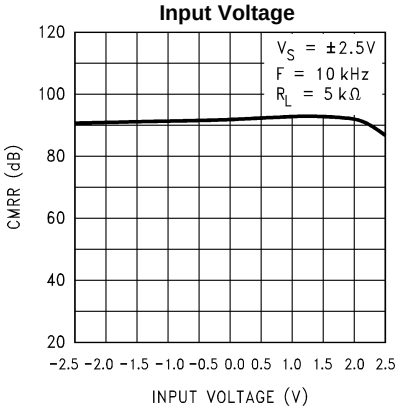


Figure 22.

CMRR vs Input Voltage

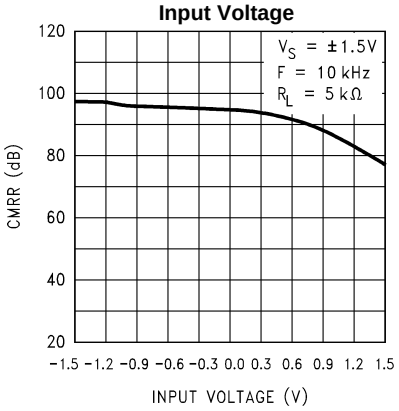


Figure 23.

ΔV_{OS} vs CMR

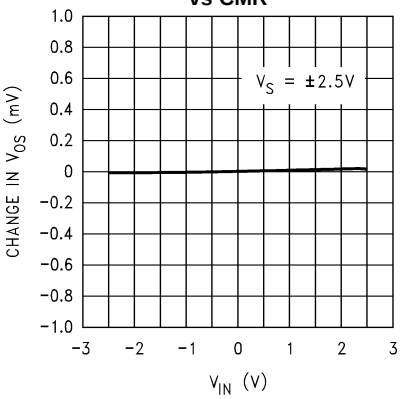


Figure 24.

ΔV_{OS} vs CMR

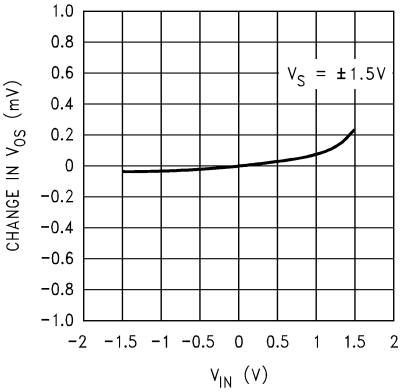


Figure 25.

Input Voltage vs Output Voltage

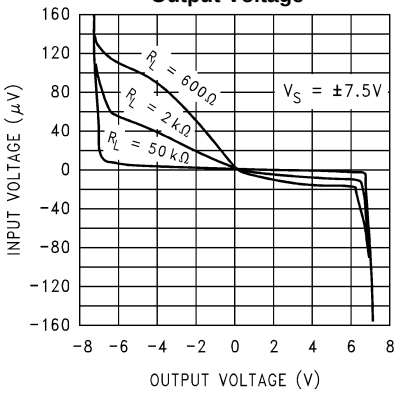


Figure 26.

Typical Performance Characteristics (continued)

V_S = +15V, Single Supply, T_A = 25°C unless otherwise specified

Input Voltage vs Output Voltage

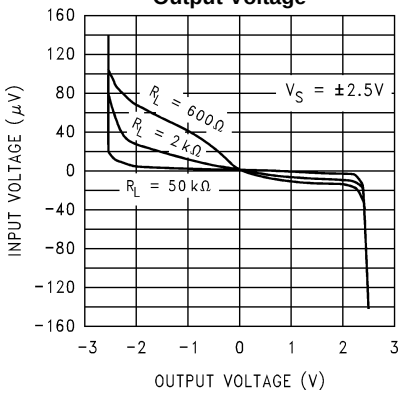


Figure 27.

Open Loop Frequency Response

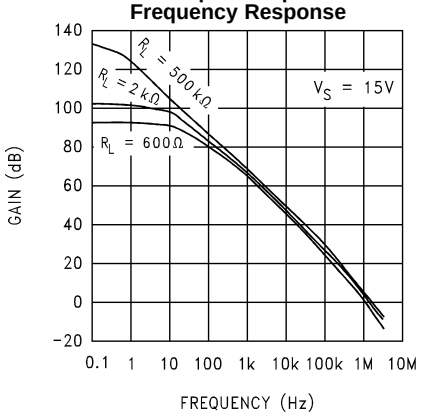


Figure 28.

Open Loop Frequency Response

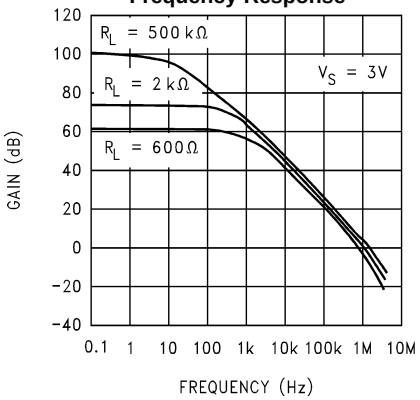


Figure 29.

Open Loop Frequency Response vs Temperature

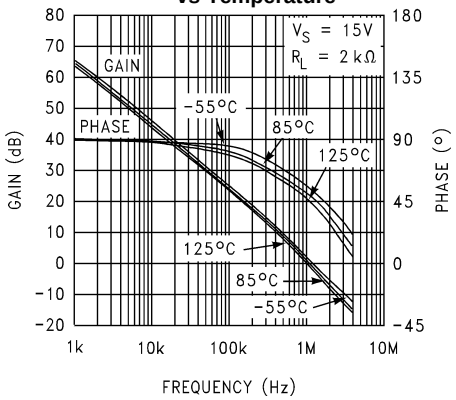


Figure 30.

Maximum Output Swing vs Frequency

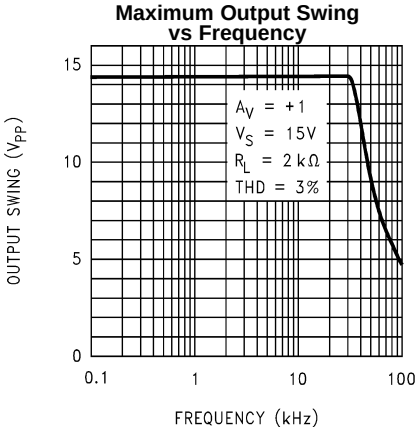


Figure 31.

Gain and Phase vs Capacitive Load

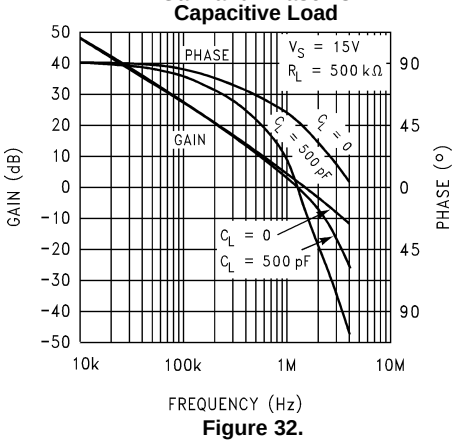


Figure 32.

Typical Performance Characteristics (continued)

V_S = +15V, Single Supply, T_A = 25°C unless otherwise specified

Gain and Phase vs Capacitive Load

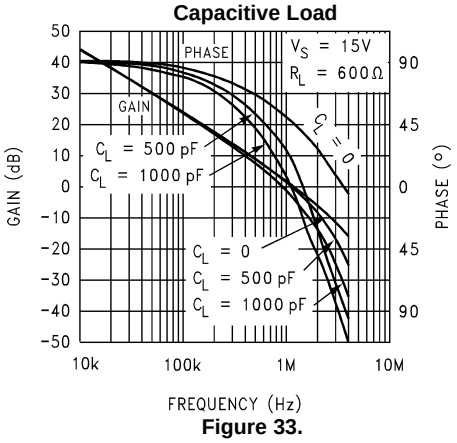


Figure 33.

Open Loop Output Impedance vs Frequency

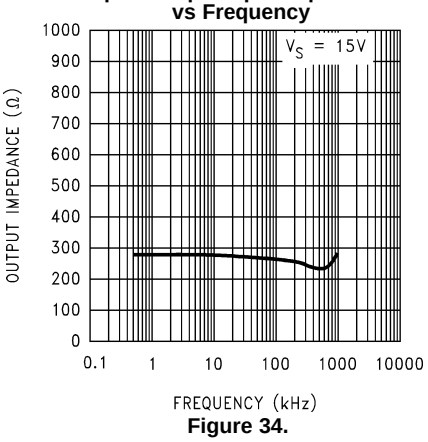


Figure 34.

Open Loop Output Impedance vs Frequency

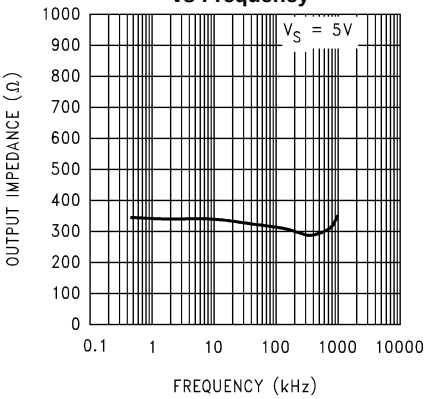


Figure 35.

Slew Rate vs Supply Voltage

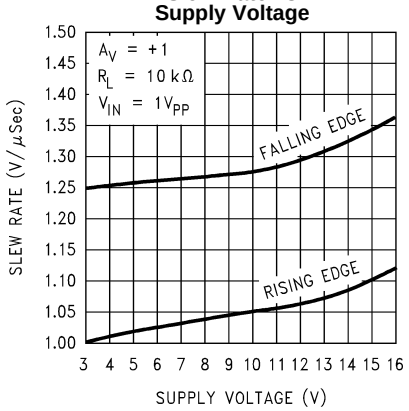


Figure 36.

Non-Inverting Large Signal Pulse Response

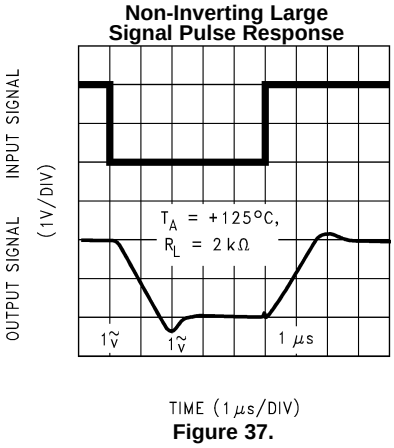


Figure 37.

Non-Inverting Large Signal Pulse Response

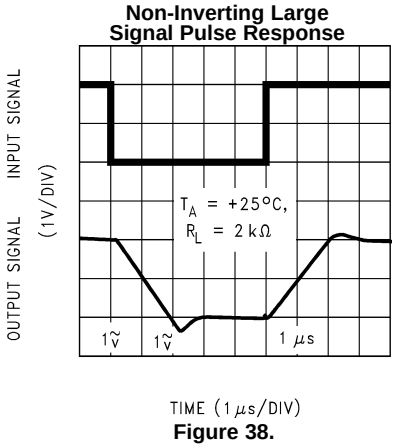


Figure 38.

Typical Performance Characteristics (continued)

V_S = +15V, Single Supply, T_A = 25°C unless otherwise specified

Non-Inverting Large Signal Pulse Response

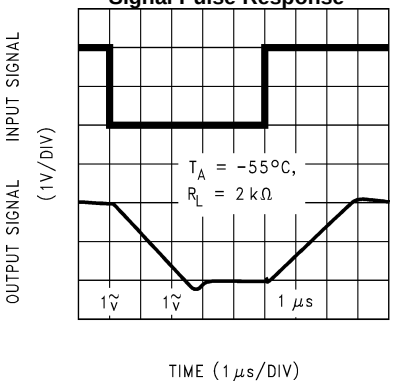


Figure 39.

Non-Inverting Small Signal Pulse Response

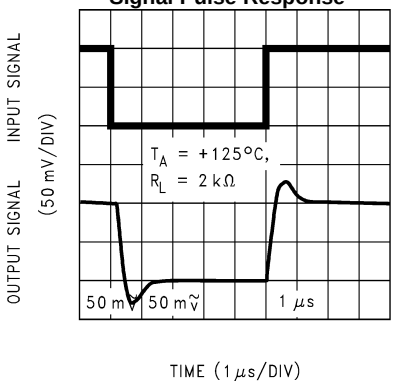


Figure 40.

Non-Inverting Small Signal Pulse Response

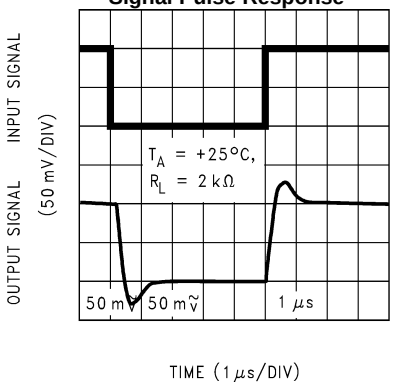


Figure 41.

Non-Inverting Small Signal Pulse Response

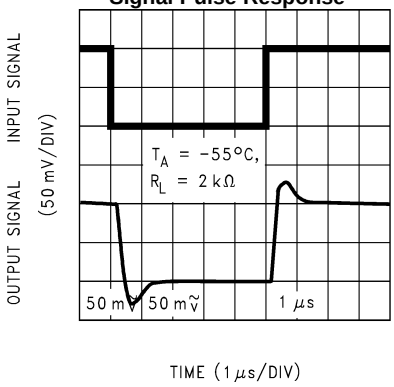


Figure 42.

Inverting Large Signal Pulse Response

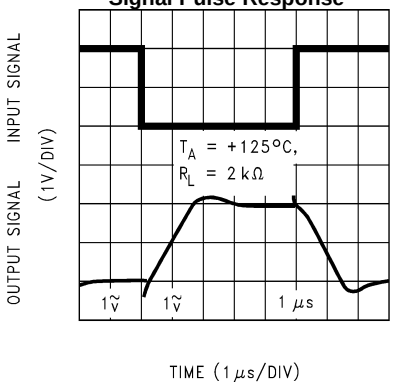


Figure 43.

Inverting Large Signal Pulse Response

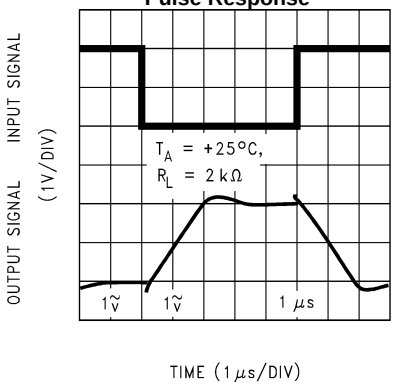


Figure 44.

Typical Performance Characteristics (continued)

V_S = +15V, Single Supply, T_A = 25°C unless otherwise specified

Inverting Large Signal Pulse Response

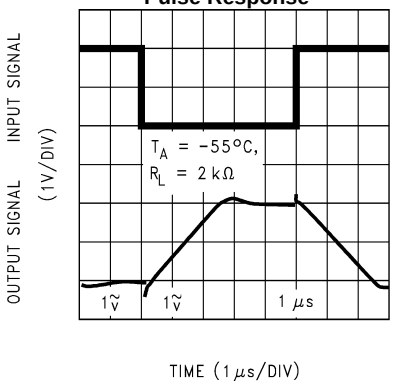


Figure 45.

Inverting Small Signal Pulse Response

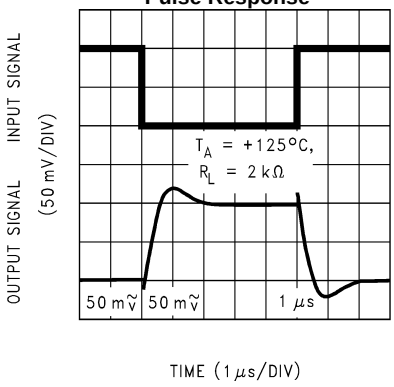


Figure 46.

Inverting Small Signal Pulse Response

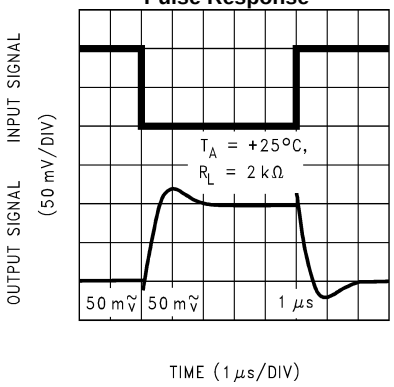


Figure 47.

Inverting Small Signal Pulse Response

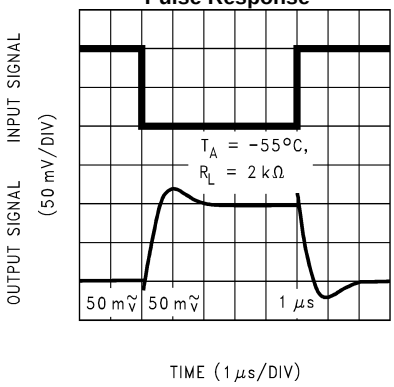


Figure 48.

Stability vs Capacitive Load

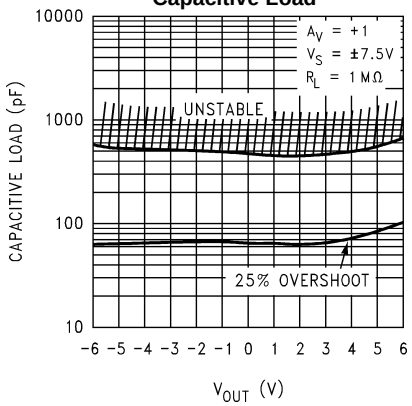


Figure 49.

Stability vs Capacitive Load

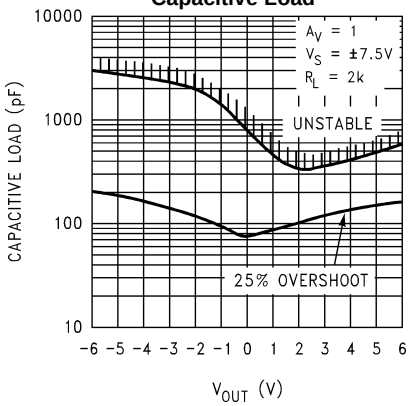


Figure 50.

Typical Performance Characteristics (continued)

V_S = +15V, Single Supply, T_A = 25°C unless otherwise specified

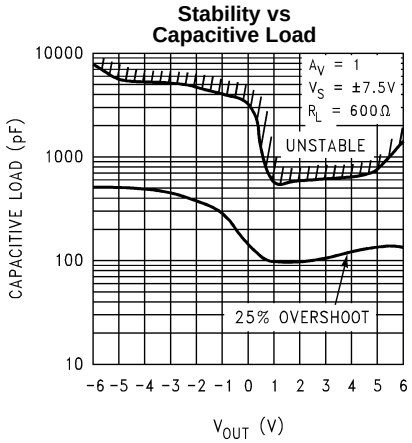


Figure 51.

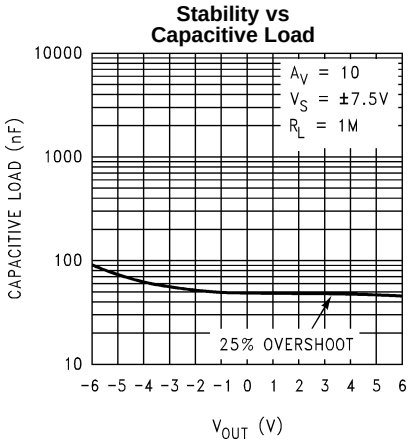


Figure 52.

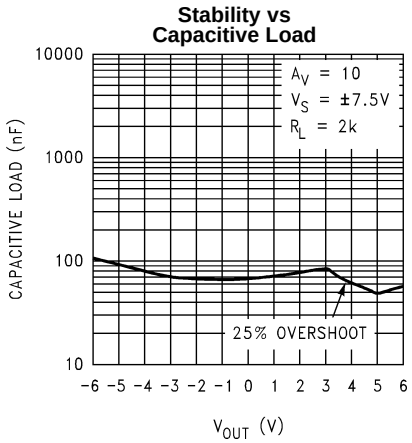


Figure 53.

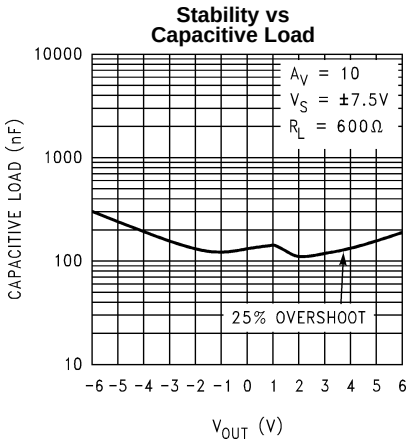


Figure 54.

APPLICATION HINTS

INPUT COMMON-MODE VOLTAGE RANGE

Unlike Bi-FET amplifier designs, the LMC6492/4 does not exhibit phase inversion when an input voltage exceeds the negative supply voltage. Figure 55 shows an input voltage exceeding both supplies with no resulting phase inversion on the output.

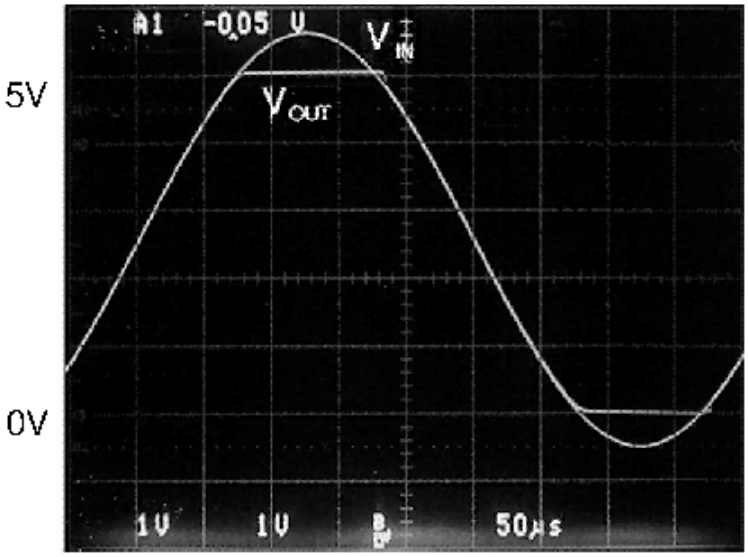


Figure 55. An Input Voltage Signal Exceeds the LMC6492/4 Power Supply Voltages with No Output Phase Inversion

The absolute maximum input voltage is 300 mV beyond either supply rail at room temperature. Voltages greatly exceeding this absolute maximum rating, as in Figure 56, can cause excessive current to flow in or out of the input pins possibly affecting reliability.

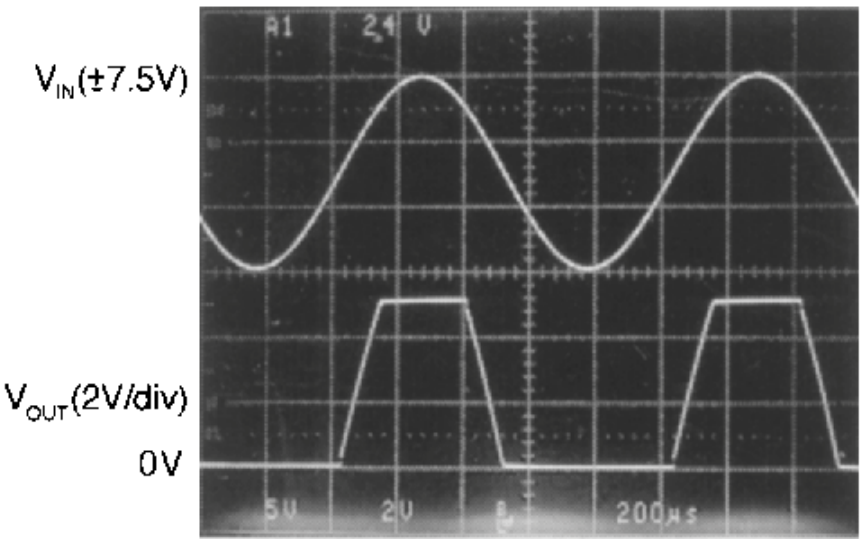


Figure 56. A ±7.5V Input Signal Greatly Exceeds the 5V Supply in Figure 57 Causing No Phase Inversion Due to R_I

Applications that exceed this rating must externally limit the maximum input current to ±5 mA with an input resistor (R_I) as shown in Figure 57.

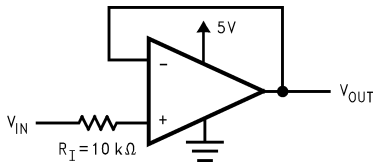


Figure 57. R_I Input Current Protection for Voltages Exceeding the Supply Voltages

RAIL-TO-RAIL OUTPUT

The approximate output resistance of the LMC6492/4 is 110Ω sourcing and 80Ω sinking at V_S = 5V. Using the calculated output resistance, maximum output voltage swing can be esitmated as a function of load.

COMPENSATING FOR INPUT CAPACITANCE

It is quite common to use large values of feedback resistance for amplifiers with ultra-low input current, like the LMC6492/4.

Although the LMC6492/4 is highly stable over a wide range of operating conditions, certain precautions must be met to achieve the desired pulse response when a large feedback resistor is used. Large feedback resistors with even small values of input capacitance, due to transducers, photodiodes, and circuit board parasitics, reduce phase margins.

When high input impedances are demanded, guarding of the LMC6492/4 is suggested. Guarding input lines will not only reduce leakage, but lowers stray input capacitance as well. (See Printed-Circuit-Board Layout for High Impedance Work).

The effect of input capacitance can be compensated for by adding a capacitor, C_f, around the feedback resistors (as in Figure 55) such that:

$$\frac{1}{2\pi R_1 C_{IN}} \geq \frac{1}{2\pi R_2 C_f} \tag{1}$$

or

$$R_1\, C_{IN} \leq R_2\, C_f \tag{2}$$

Since it is often difficult to know the exact value of C_{IN}, C_f can be experimentally adjusted so that the desired pulse response is achieved. Refer to the LMC660 and LMC662 for a more detailed discussion on compensating for input capacitance.

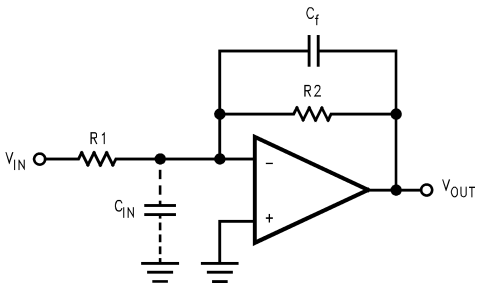


Figure 58. Cancelling the Effect of Input Capacitance

CAPACITIVE LOAD TOLERANCE

All rail-to-rail output swing operational amplifiers have voltage gain in the output stage. A compensation capacitor is normally included in this integrator stage. The frequency location of the dominant pole is affected by the resistive load on the amplifier. Capacitive load driving capability can be optimized by using an appropriate resistive load in parallel with the capacitive load (see Typical Curves).

Direct capacitive loading will reduce the phase margin of many op-amps. A pole in the feedback loop is created by the combination of the op-amp's output impedance and the capacitive load. This pole induces phase lag at the unity-gain crossover frequency of the amplifier resulting in either an oscillatory or underdamped pulse response. With a few external components, op amps can easily indirectly drive capacitive loads, as shown in Figure 59.

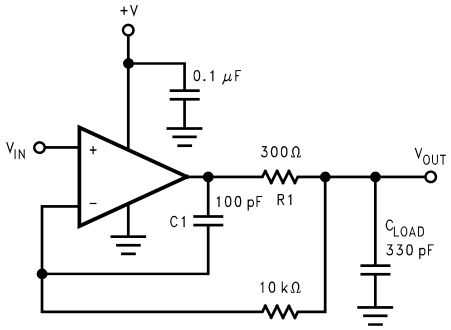


Figure 59. LMC6492/4 Noninverting Amplifier, Compensated to Handle Capacitive Loads

PRINTED-CIRCUIT-BOARD LAYOUT FOR HIGH-IMPEDANCE WORK

It is generally recognized that any circuit which must operate with less than 1000 pA of leakage current requires special layout of the PC board. When one wishes to take advantage of the ultra-low bias current of the LMC6492/4, typically 150 fA, it is essential to have an excellent layout. Fortunately, the techniques of obtaining low leakages are quite simple. First, the user must not ignore the surface leakage of the PC board, even though it may sometimes appear acceptably low, because under conditions of high humidity or dust or contamination, the surface leakage will be appreciable.

To minimize the effect of any surface leakage, lay out a ring of foil completely surrounding the LMC6492/4's inputs and the terminals of components connected to the op-amp's inputs, as in Figure 60. To have a significant effect, guard rings should be placed on both the top and bottom of the PC board. This PC foil must then be connected to a voltage which is at the same voltage as the amplifier inputs, since no leakage current can flow between two points at the same potential. For example, a PC board trace-to-pad resistance of $10^{12}\Omega$, which is normally considered a very large resistance, could leak 5 pA if the trace were a 5V bus adjacent to the pad of the input.

This would cause a 33 times degradation from the LMC6492/4's actual performance. If a guard ring is used and held within 5 mV of the inputs, then the same resistance of $10^{11}\Omega$ will only cause 0.05 pA of leakage current. See Figure 61 for typical connections of guard rings for standard op-amp configurations.

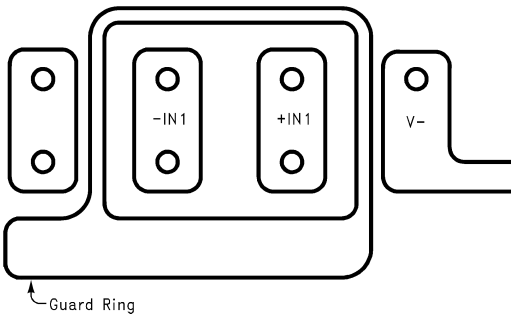


Figure 60. Examples of Guard Ring in PC Board Layout

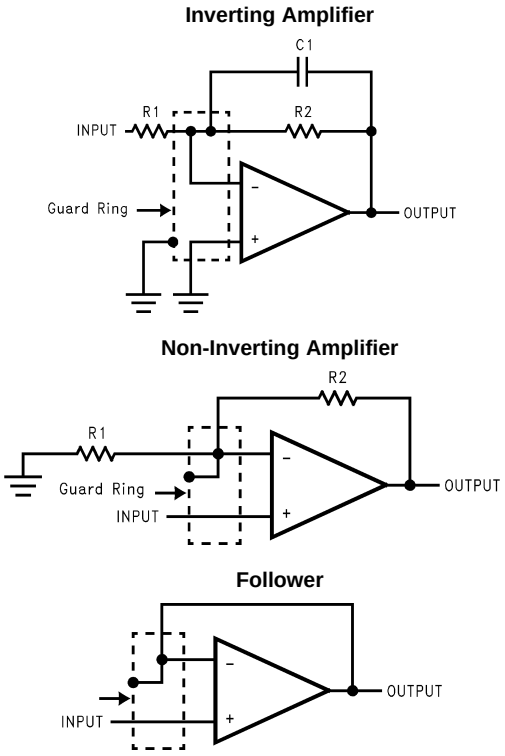
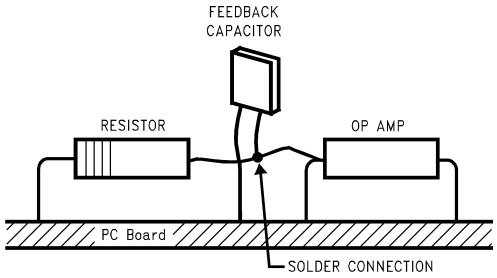


Figure 61. Typical Connections of Guard Rings

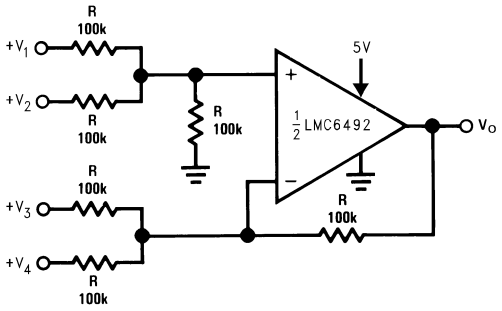
The designer should be aware that when it is inappropriate to lay out a PC board for the sake of just a few circuits, there is another technique which is even better than a guard ring on a PC board: Don't insert the amplifier's input pin into the board at all, but bend it up in the air and use only air as an insulator. Air is an excellent insulator. In this case you may have to forego some of the advantages of PC board construction, but the advantages are sometimes well worth the effort of using point-to-point up-in-the-air wiring. See Figure 62.



(Input pins are lifted out of PC board and soldered directly to components. All other pins connected to PC board).

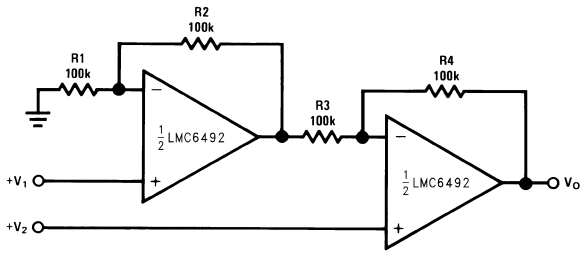
Figure 62. Air Wiring

Application Circuits



Where: $V_0 = V_1 + V_2 - V_3 - V_4$
$(V_1 + V_2 \geq (V_3 + V_4)$ to keep $V_0 > 0V_{DC}$

Figure 63. DC Summing Amplifier ($V_{IN} \geq 0V_{DC}$ and $V_O \geq V_{DC}$



For

$$\frac{R1}{R2} = \frac{R4}{R3}$$

(CMRR depends on this resistor ratio match)

$$V_O = 1 + \frac{R4}{R3}(V_2 - V_1)$$

As shown: $V_O = 2(V_2 - V_1)$

Figure 64. High Input Z, DC Differential Amplifier

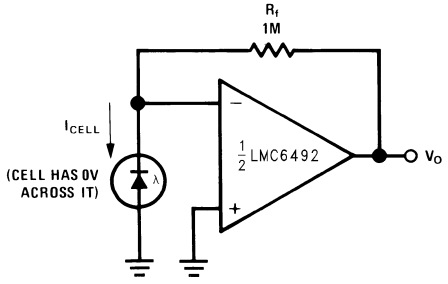
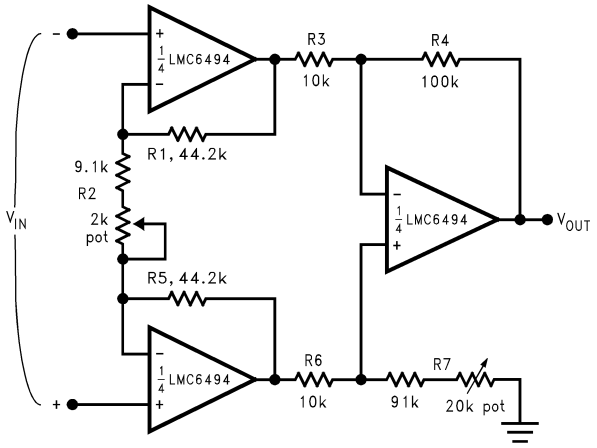


Figure 65. Photo Voltaic-Cell Amplifier

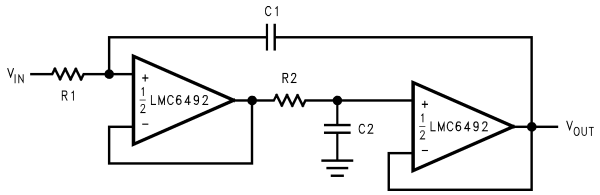


If R1 = R5, R3 = R6, and R4 = R7; then

$$\frac{V_{OUT}}{V_{IN}} = \frac{R2 + 2R1}{R2} \times \frac{R4}{R3}$$

$\therefore A_V \approx 100$ for circuit shown (R_2 = 9.3k).

Figure 66. Instrumentation Amplifier



$$R1 = R2, C1 = C2; f = \frac{1}{2\pi R1C1}; \text{Damping Factor} = \tfrac{1}{2}\sqrt{\frac{C2}{C1}}\sqrt{\frac{R2}{R1}}$$

Figure 67. Rail-to-Rail Single Supply Low Pass Filter

This low-pass filter circuit can be used as an anti-aliasing filter with the same supply as the A/D converter. Filter designs can also take advantage of the LMC6492/4 ultra-low input current. The ultra-low input current yields negligible offset error even when large value resistors are used. This in turn allows the use of smaller valued capacitors which take less board space and cost less.

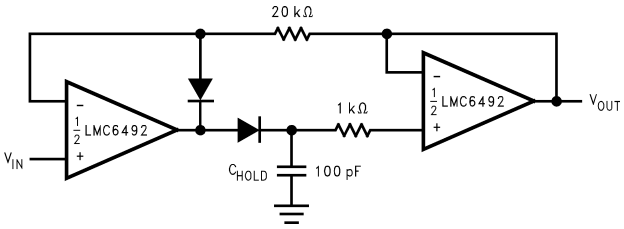
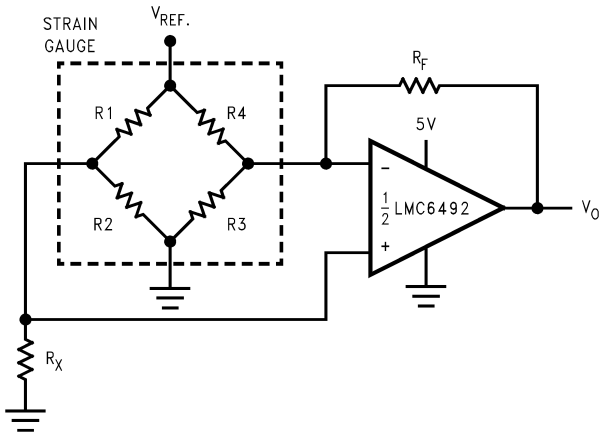


Figure 68. Low Voltage Peak Detector with Rail-to-Rail Peak Capture Range

Dielectric absorption and leakage is minimized by using a polystyrene or polypropylene hold capacitor. The droop rate is primarily determined by the value of C_H and diode leakage current. Select low-leakage current diodes to minimize drooping.



$R_f = Rx$
$R_f >>$ R1, R2, R3, and R4

$$V_O = \left(\frac{R2}{R1 + R2} - \frac{R3}{R4 + R3}\right)\frac{R_f\,(R3 + R4)}{R3\,R4}V_{REF}$$

Figure 69. Pressure Sensor

In a manifold absolute pressure sensor application, a strain gauge is mounted on the intake manifold in the engine unit. Manifold pressure causes the sensing resistors, R1, R2, R3 and R4 to change. The resistors change in a way such that R2 and R4 increase by the same amount R1 and R3 decrease. This causes a differential voltage between the input of the amplifier. The gain of the amplifier is adjusted by R_f.

Spice Macromodel

A spice macromodel is available for the LMC6492/4. This model includes accurate simulation of:

- Input common-model voltage range
- Frequency and transient response
- GBW dependence on loading conditions
- Quiescent and dynamic supply current
- Output swing dependence on loading conditions

and many other characteristics as listed on the macromodel disk.

Contact your local Texas Instruments sales office to obtain an operational amplifier spice model library disk.

REVISION HISTORY

Changes from Revision C (March 2013) to Revision D	Page
• Changed layout of National Data Sheet to TI format	20

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LMC6492AEM	NRND	SOIC	D	8	95	TBD	Call TI	Call TI	-40 to 125	LMC64 92AEM	
LMC6492AEM/NOPB	ACTIVE	SOIC	D	8	95	Green (RoHS & no Sb/Br)	SN | CU SN	Level-1-260C-UNLIM	-40 to 125	LMC64 92AEM	Samples
LMC6492AEMX/NOPB	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	SN | CU SN	Level-1-260C-UNLIM	-40 to 125	LMC64 92AEM	Samples
LMC6492BEM	NRND	SOIC	D	8	95	TBD	Call TI	Call TI	-40 to 125	LMC64 92BEM	
LMC6492BEM/NOPB	ACTIVE	SOIC	D	8	95	Green (RoHS & no Sb/Br)	SN | CU SN	Level-1-260C-UNLIM	-40 to 125	LMC64 92BEM	Samples
LMC6492BEMX	NRND	SOIC	D	8	2500	TBD	Call TI	Call TI	-40 to 125	LMC64 92BEM	
LMC6492BEMX/NOPB	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	SN | CU SN	Level-1-260C-UNLIM	-40 to 125	LMC64 92BEM	Samples
LMC6494AEM	NRND	SOIC	D	14	55	TBD	Call TI	Call TI	-40 to 125	LMC6494 AEM	
LMC6494AEM/NOPB	ACTIVE	SOIC	D	14	55	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	LMC6494 AEM	Samples
LMC6494AEMX/NOPB	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	LMC6494 AEM	Samples
LMC6494BEM	NRND	SOIC	D	14	55	TBD	Call TI	Call TI	-40 to 125	LMC6494 BEM	
LMC6494BEM/NOPB	ACTIVE	SOIC	D	14	55	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	LMC6494 BEM	Samples
LMC6494BEMX	NRND	SOIC	D	14	2500	TBD	Call TI	Call TI	-40 to 125	LMC6494 BEM	
LMC6494BEMX/NOPB	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	LMC6494 BEM	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

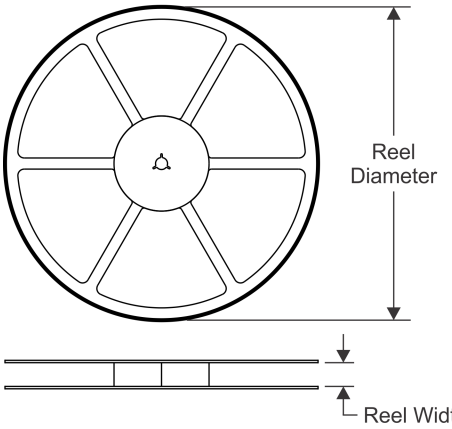
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

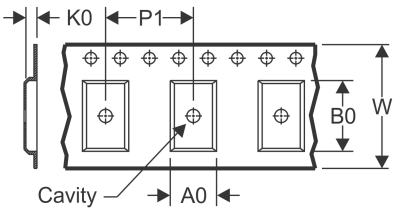
(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

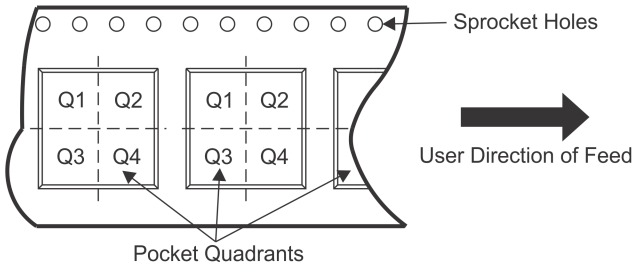


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

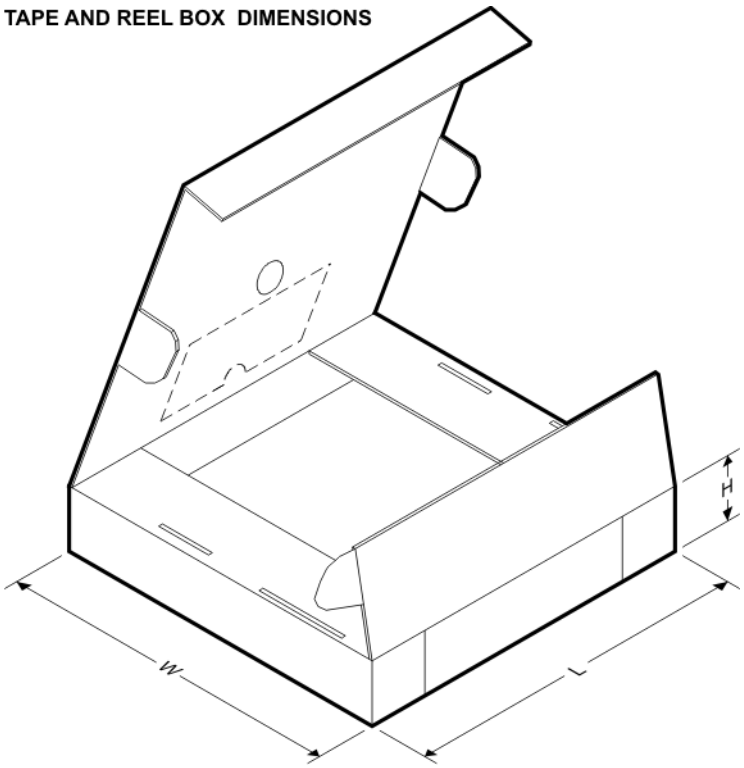
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMC6492AEMX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LMC6492BEMX	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LMC6492BEMX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LMC6494AEMX/NOPB	SOIC	D	14	2500	330.0	16.4	6.5	9.35	2.3	8.0	16.0	Q1
LMC6494BEMX	SOIC	D	14	2500	330.0	16.4	6.5	9.35	2.3	8.0	16.0	Q1
LMC6494BEMX/NOPB	SOIC	D	14	2500	330.0	16.4	6.5	9.35	2.3	8.0	16.0	Q1

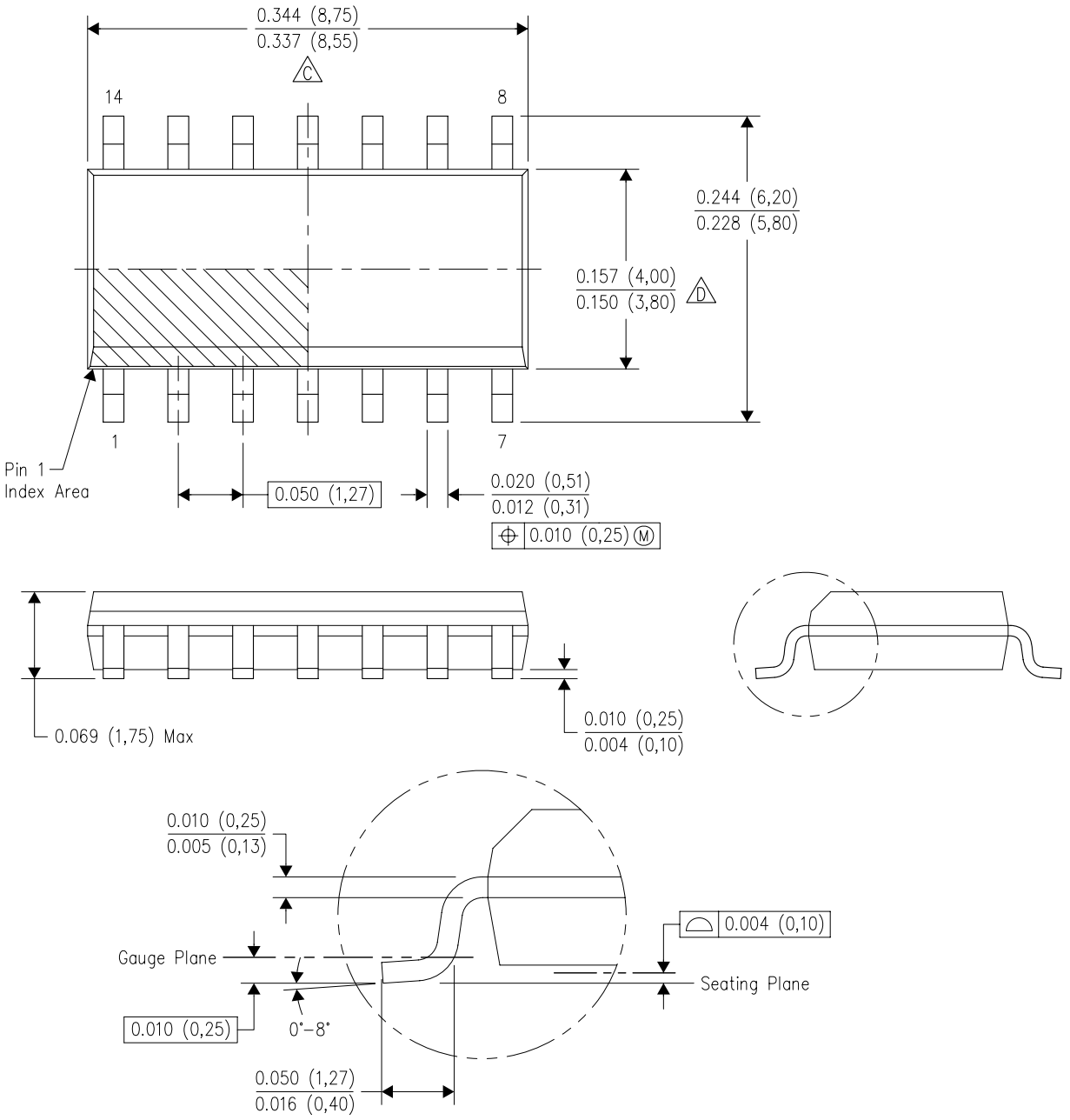
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LMC6492AEMX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0
LMC6492BEMX	SOIC	D	8	2500	367.0	367.0	35.0
LMC6492BEMX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0
LMC6494AEMX/NOPB	SOIC	D	14	2500	367.0	367.0	35.0
LMC6494BEMX	SOIC	D	14	2500	367.0	367.0	35.0
LMC6494BEMX/NOPB	SOIC	D	14	2500	367.0	367.0	35.0

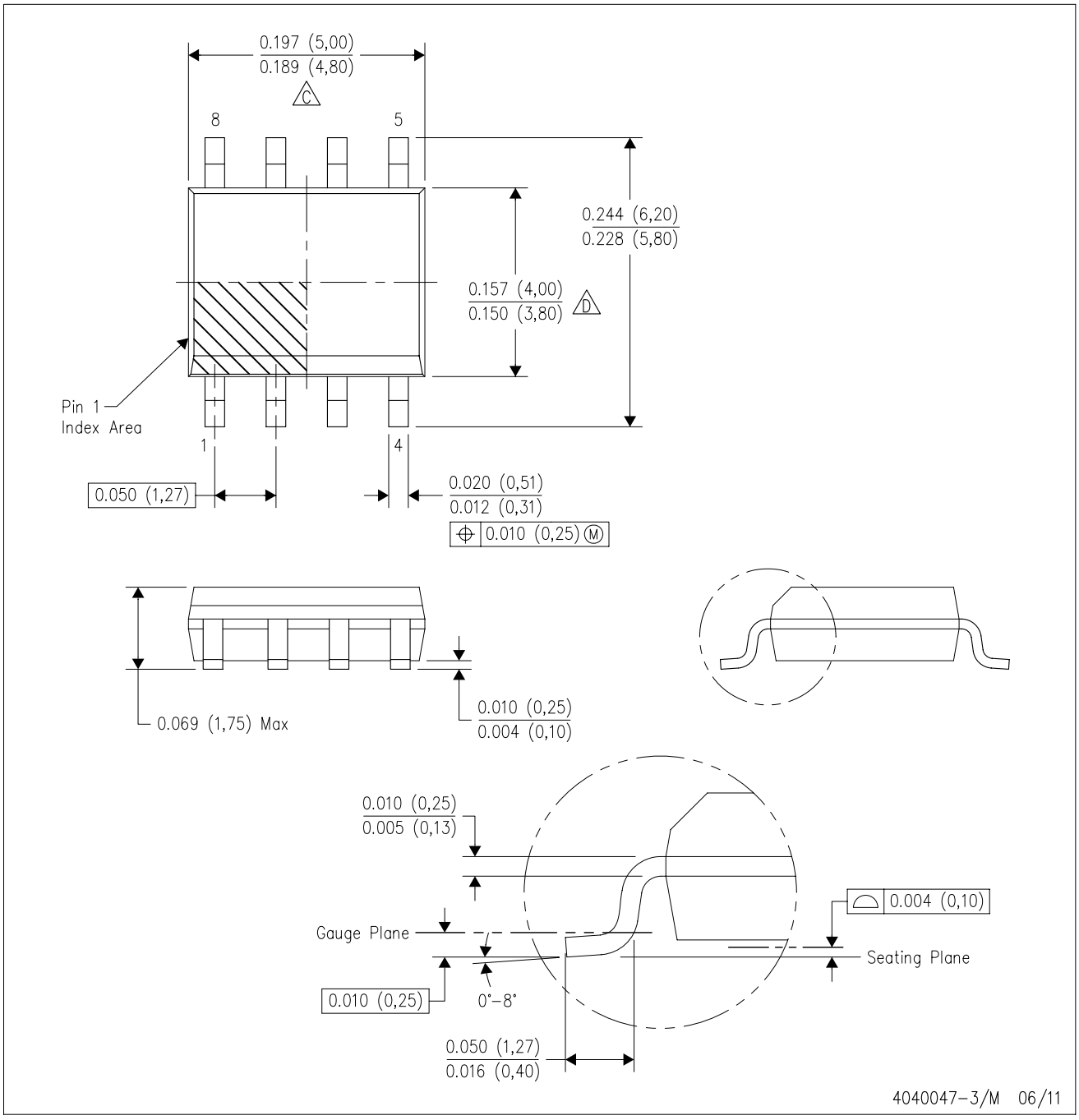
D (R–PDSO–G14) PLASTIC SMALL OUTLINE



4040047–5/M 06/11

NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AB.

D (R–PDSO–G8) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AA.

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